

DG2011

Vishay Siliconix

Low-Voltage, Low r_{ON}, Single SPDT Analog Switch In SC-89 Package

DESCRIPTION

The DG2011 is a low on-resistance, single-pole/doublethrow monolithic CMOS analog switch. It is designed for low voltage applications with guaranteed operation at 2 V. The DG2011 is ideal for portable and battery powered equipment, requiring high performance and efficient use of board space. In additional to the low on-resistance (1.8 Ω at 2.7 V), charge injection is less than 10 pC over the entire analog range.

The switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

The DG2011 is built on Vishay Siliconix's low voltage JI2 process. An epitaxial layer prevents latchup.

Break-before-make is guaranteed.

The DG2011 represents a breakthrough in packaging development for analog switching products. The SC-89 package $(1.6 \times 1.6 \text{ mm}^2)$ – also know as SOT-666 in the industry – reduces board spacing by approximately 40 % while obtaining performance comparable to SC-70 analog switch devices available today.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For analog switching products manufactured with 100 % matte tin device terminations, the lead (Pb)-free "-E3" suffix is being used as a designator.

FEATURES

- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance r_{ON} : 1.8 Ω at 2.7 V
- Low Charge Injection
- Low Voltage Logic Compatible
- SC-89 Package (1.6 x 1.6 mm)

BENEFITS

- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space
- Guaranteed 2 V Operation

APPLICATIONS

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- Battery Operated Systems
- Sample and Hold Circuits
- ADC and DAC Applications
- · Low Voltage Data Acquisition Systems

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





Device Marking: Ax x = Date/Lot Traceability Code

TRUTH TABLE					
Logic	NC	NO			
0	ON	OFF			
1	OFF	ON			

COMMERCIAL ORDERING INFORMATION					
Temp Range	Package	Part Number			
- 40 to 85 °C	SC-89 (SOT-666) with Tape and Reel	DG2011DX-T1**			
	SC-89 (SOT-666) Lead (Pb)-free with Tape and Reel	DG2011DX-T1-E3** DG2011DXA-T1-E3			

** Note:

DG2011DX-T1 and DG2011DX-T1-E3 are not recommended for new designs.

* Pb containing terminations are not RoHS compliant, exemptions may apply.





ABSOLUTE MAXIMUM RATINGS $T_A = 25 \text{ °C}$, unless otherwise noted

Parameter		Symbol	Limit	Unit		
Reference V+ to GND		- 0.3 to + 6	N			
IN, COM, NC, NO ^a			- 0.3 to (V+ + 0.3 V)	V		
Continuous Current (NO, NC, COM pins)			± 150	m 4		
Peak Current (Pulsed at 1 ms, 10 % duty cycle)			± 300	IIIA		
Storage Temperature	D Suffix		- 65 to 150	°C		
Power Dissipation (Packages) ^b	SC-89 ^c		172	mW		

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC Board.

c. Derate 2.15 mW/°C above 70 °C.

SPECIFICATIONS (V+ = 2.0 V)								
		Test Conditions		Limits				
		Otherwise Unless Specified		- 40 to 85 °C				
Parameter	Symbol	V + = 2.0 V, V_{IN} = 0.4 V or 1.6 V^{e}	Temp ^a	Min ^b	Тур ^с	Max ^b	Unit	
Analog Switch								
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	v	
On-Resistance	r _{ON}	V+ = 2.0 V, V _{COM} = 0.2 V/0.9 V I _{NO} , I _{NC} = 20 mA	Room Full		3.5	5.5 5.5	Ω	
Switch Off Leakage Current ^f	I _{NO(off)} I _{NC(off)}	V+ = 2.2 V,		- 1 - 10		1 10		
	I _{COM(off)}	V _{NO} , V _{NC} = 0.5 V/1.5 V, V _{COM} = 1.5 V/0.5 V	Room Full	- 1 - 10		1 10	nA	
Channel-On Leakage Current ^f	I _{COM(on)}	V+ = 2.2 V, V _{NO} , V _{NC} = V _{COM} = 0.5 V/1.5 V	Room Full	- 1 - 10		1 10		
Digital Control								
Input High Voltage	V _{INH}		Full	1.5			v	
Input Low Voltage	V _{INL}		Full			0.4	•	
Input Capacitance	C _{in}		Full		4		pF	
Input Current	I _{INL} or I _{INH}	$V_{IN} = 0 \text{ or } V+$	Full	1		1	μA	
Dynamic Characteristics								
Turn-On Time	t _{ON}		Room Full		75	110 113		
Turn-Off Time	t _{OFF}	V_{NO} or V_{NC} = 1.5 V, R_L = 300 Ω , C_L = 35 pF	Room Full		37	71 76	ns	
Break-Before-Make Time	t _{BBM}		Room	1	37			
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_GEN = 0 V, R_GEN = 0 Ω	Room		7		рС	
Off-Isolation ^d	OIRR	$B_{1} = 50 \Omega C_{2} = 5 pE f = 1 MHz$	Room		- 62		dD	
Crosstalk ^d	X _{TALK}	$h_{L} = 30.32, 0L = 3.01, 1 = 1.0012$	Room		- 69		uБ	
N _O , N _C Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		29		pF	
Channel-On Capacitance ^d	C _{ON}		Room		85			
Power Supply								
Positive Supply Range	V+	$V_{\rm eff} = 0$ or $V_{\rm eff}$		1.8		5.5	V	
Negative Supply Current	l+				0.01	1.0	μA	



SPECIFICATIONS (V+	= 3 V)						
		Test Conditions Otherwise Unless Specified		Limits -40 to 85 °C			
Parameter	Symbol	V+ = 3 V, ± 10 %, V _{IN} = 0.4 V or 2.0 V ^e	Temp ^a	Min ^b	Тур ^с	Max ^b	Unit
Analog Switch	1 -						
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	v
On-Resistance	r _{ON}		Room Full		1.8	2.7 2.9	Ω
r _{ON} Match	∆r _{ON}	$v_{+} = 2.7 v, v_{COM} = 0.9 v/1.5 v$	Room			0.2	
r _{ON} Flatness	r _{ON} Flatness	NO, NC - 50 MA	Room		0.2	0.5	
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}	V+ = 3.3 V, V _{NO} , V _{NC} = 1 V/3 V, V _{COM} = 3 V/1 V	Room Full	- 1 - 10		1 10	nA
Switch On Leakage Current	I _{COM(off)}		Room Full	- 1 - 10		1 10	
Channel-On Leakage Current ^f	I _{COM(on)}	V+ = 3.3 V, V _{NO} , V _{NC} = V _{COM} = 1 V/3 V	Room Full	- 1 - 10		1 10	
Digital Control	•					•	
Input High Voltage	V _{INH}		Full	1.6			V
Input Low Voltage	V _{INL}		Full			0.4	
Input Capacitance	C _{in}		Full		4		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	1		1	μA
Dynamic Characteristics							
Turn-On Time	t _{ON}		Room Full		45	75 77	
Turn-Off Time	tOFF	$V_{NO} \text{ or } V_{NC} = 2.0 \text{ V}, \text{ R}_{L} = 300 \Omega, \text{ C}_{L} = 35 \text{ pF}$	Room Full		29	59 62	ns
Break-Before-Make Time	t _{BBM}		Room	1	16		
Charge Injection ^d	Q _{INJ}	${\sf C}_{\sf L}$ = 1 nF, ${\sf V}_{\sf GEN}$ = 0 V, ${\sf R}_{\sf GEN}$ = 0 Ω	Room		2		рС
Off-Isolation ^d	OIRR	$B_{-50,0,0} = 5 \text{ pE } f = 1 \text{ MHz}$	Room		- 62		dD
Crosstalk ^d	X _{TALK}	$h_{L} = 30.32, O_{L} = 3.01, T = 1.0012$	Room		- 68		aв
N _O , N _C Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		28		pF
Channel-On Capacitance ^d	C _{ON}		Room		84		1
Power Supply		1					
Power Supply Range	V+			1.8		5.5	V
Power Supply Current	l+	$V_{\rm m} = 0$ or $V_{\rm m}$			0.01	1.0	μA
Power Consumption	P _C					3.3	μW

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. Typical values are for design aid only, not guaranteed nor subject to production testing.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Guarantee by design, nor subjected to production test.

e. V_{IN} = input voltage to perform proper function.

f. Guaranteed by 5 V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS $T_A = 25 \text{ °C}$, unless otherwise noted



Leakage Current vs. Temperature





Supply Current vs. Input Switching Frequency





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TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted





Q - Charge Injection (pC)

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TEST CIRCUITS

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$

Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

C_L (includes fixture and stray capacitance)

Figure 1. Switching Time

Logic

Input

 $V_{NC} = V_{NO}$

Switch

Output

3 V

0 V

Vo

0 V

90%

t_D

IN depends on switch configuration: input polarity determined by sense of switch.

t_r <5 ns t_f <5 ns

t_D

TEST CIRCUITS

Figure 4. Off-Isolation

Figure 5. Channel Off/On Capacitance

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